

ABSTRACT

A bond pad structure comprising two bond pads, methods of forming the bond pad structure, an integrated circuit die incorporating the bond pad structure, and methods of using the bond pad structure are provided. Each of the bond pads comprise stacked metal layers, at least one lower metal layer and an upper metal layer. When the two pads are connected by a conductive material, they function as a single pad. The lower metal layer of one of the bond pads forms an extension that extends beneath the upper metal layer of the other of the bond pad. The lower metal extension functions to block the etching of a dielectric layer that is put down over the upper metal layers and the underlying substrate, for example, during a passivation etch to form the bond pad opening, to protect the substrate from damage.

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